

TENTATIVE

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7WH08FU, TC7WH08FK

(UNDER DEVELOPMENT)

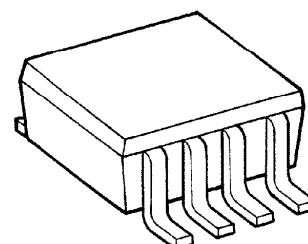
DUAL 2-INPUT AND GATE

The TC7WH08 is an advanced high speed CMOS 2-INPUT AND GATE fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

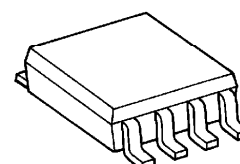
- High Speed $t_{pd} = 4.3\text{ns}$ (Typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation $I_{CC} = 2\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC}(\text{opr}) = 2 \sim 5.5\text{V}$

TC7WH08FU



SSOP8-P-0.65

TC7WH08FK

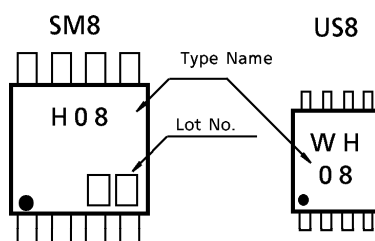


SSOP8-P-0.50A

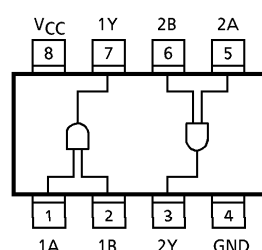
Weight

SSOP8-P-0.65 : 0.02g (Typ.)
 SSOP8-P-0.50A : 0.01g (Typ.)

MARKING



PIN ASSIGNMENT (TOP VIEW)



980508EBA1

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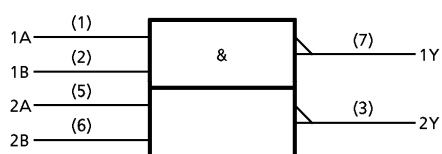
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● The information contained herein is subject to change without notice.

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|------------------------------------|------------------|---------------------------|------|
| Supply Voltage Range | V _{CC} | -0.5~7.0 | V |
| DC Input Voltage | V _{IN} | -0.5~7.0 | V |
| DC Output Voltage | V _{OUT} | -0.5~V _{CC} +0.5 | V |
| Input Diode Current | I _{IK} | -20 | mA |
| Output Diode Current | I _{OK} | ±20 | mA |
| DC Output Current | I _{OUT} | ±25 | mA |
| DC V _{CC} /Ground Current | I _{CC} | ±50 | mA |
| Power Dissipation | P _D | 300 (SM8) | mW |
| | | 200 (US8) | |
| Storage Temperature | T _{stg} | -65~150 | °C |
| Lead Temperature (10 s) | T _L | 260 | °C |

LOGIC DIAGRAM



TRUTH TABLE

| A | B | Y |
|---|---|---|
| L | L | L |
| L | H | L |
| H | L | L |
| H | H | H |

RECOMMENDED OPERATING CONDITIONS

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|--------------------------|------------------|--------------------------------------|------|
| Supply Voltage | V _{CC} | 2.0~5.5 | V |
| Input Voltage | V _{IN} | 0~5.5 | V |
| Output Voltage | V _{OUT} | 0~V _{CC} | V |
| Operating Temperature | T _{opr} | -40~85 | °C |
| Input Rise and Fall Time | dt/dv | 0~100 (V _{CC} = 3.3 ± 0.3V) | ns/V |
| | | 0~20 (V _{CC} = 5 ± 0.5V) | |

DC ELECTRICAL CHARACTERISTICS

| CHARACTERISTIC | SYMBOL | TEST CONDITION | | V _{CC} (V) | Ta = 25°C | | | Ta = −40~85°C | | UNIT |
|---------------------------|-----------------|---------------------------------------------------------|-------------------------|------------------------|----------------------------------|--------|----------------------------------|----------------------------------|----------------------------------|------|
| | | | | | MIN. | TYP. | MAX. | MIN. | MAX. | |
| High-Level Input Voltage | V _{IH} | — | | 2.0 3.0~ 5.5 | 1.50 V _{CC} × 0.7 | — — | — — | 1.50 V _{CC} × 0.7 | — — | V |
| Low-Level Input Voltage | V _{IL} | — | | 2.0 3.0~ 5.5 | — — | — — | 0.50 V _{CC} × 0.3 | — — | 0.50 V _{CC} × 0.3 | V |
| High-Level Output Voltage | V _{OH} | V _{IN} = V _{IH} | I _{OH} = −50μA | 2.0 | 1.9 | 2.0 | — | 1.9 | — | V |
| | | | | 3.0 | 2.9 | 3.0 | — | 2.9 | — | |
| | | | | 4.5 | 4.4 | 4.5 | — | 4.4 | — | |
| | | | I _{OH} = −4mA | 3.0 | 2.58 | — | — | 2.48 | — | |
| | | | | I _{OH} = −8mA | 4.5 | 3.94 | — | — | 3.80 | |
| Low-Level Output Voltage | V _{OL} | V _{IN} = V _{IH} or V _{IL} | I _{OL} = 50μA | 2.0 | — | 0.0 | 0.1 | — | 0.1 | V |
| | | | | 3.0 | — | 0.0 | 0.1 | — | 0.1 | |
| | | | | 4.5 | — | 0.0 | 0.1 | — | 0.1 | |
| | | | I _{OL} = 4mA | 3.0 | — | — | 0.36 | — | 0.44 | |
| | | | | I _{OL} = 8mA | 4.5 | — | — | 0.36 | — | |
| Input Leakage Current | I _{IN} | V _{IN} = 5.5V or GND | | 0~ 5.5 | — | — | ± 0.1 | — | ± 1.0 | μA |
| Quiescent Supply Current | I _{CC} | V _{IN} = V _{CC} or GND | | 5.5 | — | — | 2.0 | — | 20.0 | μA |

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | Ta = 25°C | | | Ta = -40~85°C | | UNIT |
|-------------------------------|--------------------------------------|----------------|---------------------|---------------------|------|---------------|------|------|
| | | | V _{CC} (V) | C _L (pF) | MIN. | TYP. | MAX. | |
| Propagation Delay Time | t _{pLH} t _{pHL} | — | 3.3 ± 0.3 | 15 | — | 6.2 | 8.8 | ns |
| | | | | 50 | — | 8.7 | 12.3 | |
| | | | 5.0 ± 0.5 | 15 | — | 4.3 | 5.9 | |
| | | | | 50 | — | 5.8 | 7.9 | |
| Input Capacitance | C _{IN} | — | — | — | — | 4 | 10 | pF |
| Power Dissipation Capacitance | C _{PD} | (Note 1) | — | — | — | 18 | — | pF |

(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

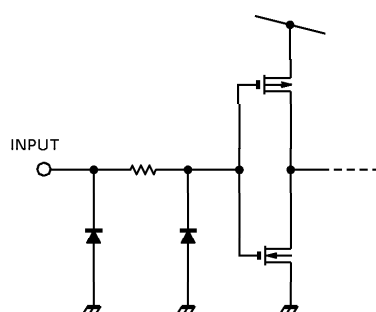
Average operating current can be obtained by the equation :

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

NOISE CHARACTERISTICS (Ta = 25°C, Input $t_r = t_f = 3\text{ns}$)

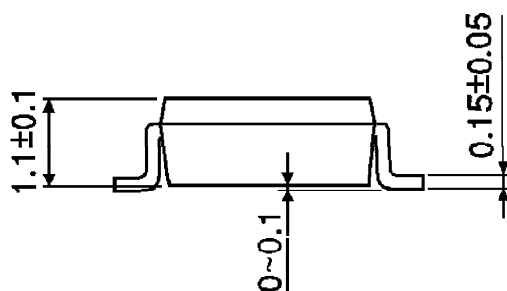
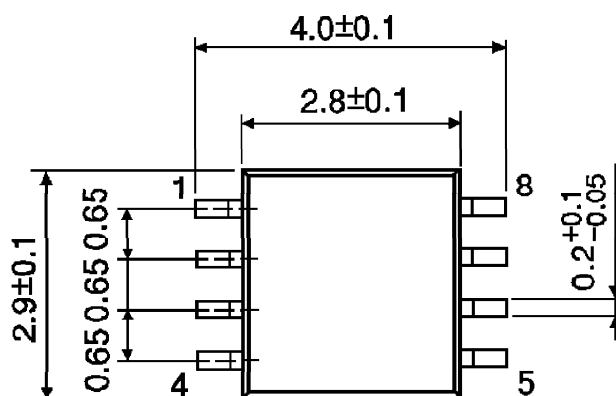
| CHARACTERISTIC | SYMBOL | TEST CONDITION | V _{CC} (V) | TYP. | LIMIT | UNIT |
|-------------------------------------------------|------------------|-----------------------|---------------------|------|-------|------|
| | | | | | | |
| Quiet Output Maximum Dynamic V _{OL} | V _{OLP} | C _L = 50pF | 5.0 | 0.3 | 0.8 | V |
| Quiet Output Minimum Dynamic V _{OL} | V _{OLV} | C _L = 50pF | 5.0 | −0.3 | −0.8 | V |
| Minimum High Level Dynamic Input Voltage | V _{IHD} | C _L = 50pF | 5.0 | — | 3.5 | V |
| Maximum Low Level Dynamic Input Voltage | V _{ILD} | C _L = 50pF | 5.0 | — | 1.5 | V |

INPUT EQUIVALENT CIRCUIT



OUTLINE DRAWING
SSOP8-P-0.65

Unit : mm



Weight : 0.02g (Typ.)

